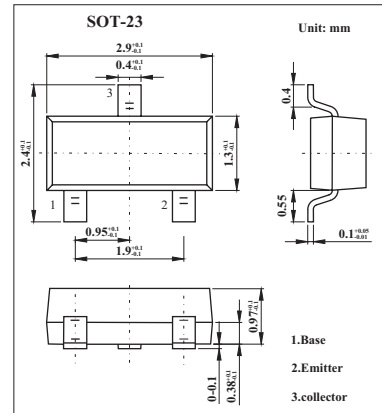


■ Features

- SOT23 NPN silicon planar medium



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	170	V
Collector-emitter voltage	V <sub>CEO</sub>	150	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Peak collector current	I <sub>CM</sub>	2	A
Collector current	I <sub>C</sub>	1	A
Base current	I <sub>B</sub>	200	mA
Power dissipation	P <sub>tot</sub>	500	mW
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	Ic=100μA	170			V
Collector-emitter breakdown voltage *	V(BR)CEO	Ic=10mA	150			V
Emitter-base breakdown voltage	V(BR)EBO	Ie=100μA	5			V
Collector Cut-Off Currents	IcBO	Vcb=150V			100	nA
Collector Cut-Off Currents	IcES	Vce=150V			100	nA
Emitter cut-off current	IeBO	VEB=4V			100	nA
Collector-emitter saturation voltage *	VCE(sat)	Ic=250mA, Ib=25mA Ic=500mA, Ib=50mA			0.2 0.3	V
Base-emitter saturation voltage *	VBE(sat)	Ic=500mA, Ib=50mA			1.0	V
Base-emitter voltage *	VBE(ON)	Ic=500mA, Vce=10V			1.0	V
Static Forward Current Transfer Ratio	hFE	Ic=1mA, Vce=10V	100			
		Ic=250mA, Vce=10V*	100		300	
		Ic=500mA, Vce=10V*	50			
		Ic=1A, Vce=10V*	10			
Transition Frequency	fT	Ic=50mA, Vce=10V, f=100MHz	100			MHz
Collector-Base Breakdown Voltage	Cobo	Vcb=10V, f=1MHz			10	pF

\* Pulse test: tp = 300 μs; d ≤ 0.02.